

TRANSISTOR(PNP)

FEATURES

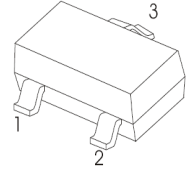
- Driver Transistors

MARKING:2H

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-4	V
I_C	Collector Current	-500	mA
P_C	Collector Power Dissipation	225	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	556	$^{\circ}\text{C/W}$
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

SOT - 23



1. BASE
2. EMITTER
3. COLLECTOR

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}$, $I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}$, $I_B=0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}$, $I_C=0$	-4			V
Collector cut-off current	I_{CBO}	$V_{CB}=-60\text{V}$, $I_E=0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-60\text{V}$, $I_B=0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1\text{V}$, $I_C=-10\text{mA}$	100			
	$h_{FE(2)}$	$V_{CE}=-1\text{V}$, $I_C=-100\text{mA}$	100			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100\text{mA}$, $I_B=-10\text{mA}$			-0.25	V
Base-emitter voltage	V_{BE}	$V_{CE}=-1\text{V}$, $I_C=-100\text{mA}$			-1.2	V
Transition frequency	f_T	$V_{CE}=-1\text{V}$, $I_C=-100\text{mA}$, $f=100\text{MHz}$	50			MHz